

Vishay Siliconix

16 Ω , Low Parasitic Capacitance and Leakage, +12 V / +5 V / +3 V / ± 5 V Quad SPST Switches

DESCRIPTION

The DG411LE, DG412LE, and DG413LE are monolithic quad single-pole-single-throw analog switches. The DG411LE and DG412LE differ only in that they respond to opposite logic levels. The DG413LE has two normally open and two normally closed switches. It can be given various configurations, including four SPST, two SPDT, and one DPDT.

The DG411LE, DG412LE, and DG413LE offer low on resistance of 16 Ω , low parasitic capacitance of 15 pF switch on capacitance, and low charge injection over the signal swing range.

The DG411LE, DG412LE, and DG413LE operate on single and dual supplies. Single supply voltage ranges from 3 V to 16 V while dual supply operation is recommended with \pm 3 V to \pm 8 V. Each switch conducts equally well in both direction when on, and blocks input voltages up to the supply levels when off.

The DG411LE, DG412LE, and DG413LE are available in 16 lead TSSOP, SOIC, and PDIP packages.

FEATURES

 3 V to 16 V single supply or ± 3 V to ± 8 V dual supply



• On-resistance $R_{DS(on)}$: 16 Ω

• Low parasitic capacitance:

C_{D(ON)}: 15 pF C_{S(OFF)}: 5 pF

 Less than 8 pC charge injection over the full signal swing range

 Fast switching t_{ON}: 16 ns t_{OFF}: 9 ns

• TTL, CMOS compatible

 Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

BENEFITS

- Wide operation voltage range
- Low signal errors and distortion
- · Fast switching time
- Minimized switching glitch

APPLICATIONS

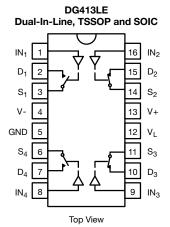
- · Automatic test equipment
- · Data acquisition systems
- Meters and instruments
- Medical and healthcare systems
- Communication systems
- · Audio and video signal routing
- Relay replacement
- Battery powered systems
- Computer peripherals
- · Audio and video signal routing

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION

Dual-In-Line, TSSOP and SOIC IN₁ IN₂ D_2 D₁ Sı S_2 V-V٠ V_L **GND** S_3 S_4 D_4 D_3 IN_4

Top View

DG411LE, DG412LE



Document Number: 78091



DG411LE, DG412LE, DG413LE

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| TRUTH TABLE | | | | | | | | |
|-------------|---------|---------|--|--|--|--|--|--|
| LOGIC | DG411LE | DG412LE | | | | | | |
| 0 | ON | OFF | | | | | | |
| 1 | OFF | ON | | | | | | |

Logic "0" \leq 0.8 V Logic "1" \geq 2.4 V

| TRUTH TABLE | | | | | | | |
|-------------|-----------------------------------|-----------------------------------|--|--|--|--|--|
| LOGIC | SW ₁ , SW ₄ | SW ₂ , SW ₃ | | | | | |
| 0 | OFF | ON | | | | | |
| 1 | ON | OFF | | | | | |

 $\begin{array}{l} Logic~"0" \leq 0.8~V \\ Logic~"1" \geq 2.4~V \end{array}$

| ORDERING INFORMATION | | | | | | | | |
|-------------------------------|---------------|----------------|------------------|-----------------------------|--|--|--|--|
| TEMP. RANGE | CONFIGURATION | PACKAGE | PART NUMBER | MIN. ORDER / PACK. QUANTITY | | | | |
| | | 16-pin TSSOP | DG411LEDQ-GE3 | Tube 360 units | | | | |
| | | 10-рін 1330Р | DG411LEDQ-T1-GE3 | Tape and reel, 3000 units | | | | |
| | DG411LE | 10 -i- 0010 | DG411LEDY-GE3 | Tube 500 units | | | | |
| | | 16-pin SOIC | DG411LEDY-T1-GE3 | Tape and reel, 2500 units | | | | |
| | | 16-pin PDIP | DG411LEDJ-GE3 | Tube 500 units | | | | |
| | | 16-pin TSSOP - | DG412LEDQ-GE3 | Tube 360 units | | | | |
| 40.00 | | | DG412LEDQ-T1-GE3 | Tape and reel, 3000 units | | | | |
| -40 °C to +85 °C Lead-free | DG412LE | | DG412LEDY-GE3 | Tube 500 units | | | | |
| Load 1100 | | | DG412LEDY-T1-GE3 | Tape and reel, 2500 units | | | | |
| | | 16-pin PDIP | DG412LEDJ-GE3 | Tube 500 units | | | | |
| | | 16 pin TSSOD | DG413LEDQ-GE3 | Tube 360 units | | | | |
| | | 16-pin TSSOP | DG413LEDQ-T1-GE3 | Tape and reel, 3000 units | | | | |
| | DG413LE | 16-pin SOIC | DG413LEDY-GE3 | Tube 500 units | | | | |
| | | 10-ріп 3010 | DG413LEDY-T1-GE3 | Tape and reel, 2500 units | | | | |
| | | 16-pin PDIP | DG413LEDJ-GE3 | Tube 500 units | | | | |

| ABSOLUTE MAXIMUM RATINGS | | | | | | | |
|---|----------------------------|---|------|--|--|--|--|
| PARAMETER | | LIMIT | UNIT | | | | |
| V+ to V- | | -0.3 to +18 | | | | | |
| GND to V- | | 18 | 7 | | | | |
| V _L | | (GND -0.3) to (V+) +0.3 | V | | | | |
| I _N a, V _S , V _D | | -0.3 to (V+) +0.3 or 30 mA, whichever occurs first | | | | | |
| Continuous Current (Any terminal) | | 30 | A | | | | |
| Peak Current, S or D (Pulsed 1 ms, 10 % du | ity cycle) | 100 | mA | | | | |
| Storage Temperature | (DQ, DY suffix) | -65 to +125 | °C | | | | |
| Storage remperature | (AK suffix) | -65 to +150 | 7 | | | | |
| | 16-pin TSSOP ^c | 450 | | | | | |
| Power Dissipation (Packages) b | 16-pin SOIC ^d | 650 | mW | | | | |
| | 16-pin CerDIP ^e | 900 | 7 | | | | |
| ESD Human Body Model (HBM); per ANSI / | ESDA / JEDEC® JS-001 | 2500 | V | | | | |
| Latch Up Current, per JESD78D | | 400 | mA | | | | |

Notes

- a. Signals on S_X, D_X, or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings
- b. All leads welded or soldered to PC board
- c. Derate 7 mW/°C above 75 °C
- d. Derate 7.6 mW/°C above 75 °C
- e. Derate 12 mW/°C above 75 °C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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| SPECIFICATIONS ^a (Single Supply 12 V) | | | | | | | | | |
|--|---------------------|---|--------------|--------|--------|----------------------------|--------|---------------------------|------|
| PARAMETER | SYMBOL | TEST CONDITIONS UNLESS OTHERWISE SPECIFIED | TEMP. b | TYP. ° | LIM | IFFIX IITS 0 +125 °C | LIM | IFFIX IITS o +85 °C | UNIT |
| | | $V_{+} = 12 \text{ V}, V_{-} = 0 \text{ V}$ $V_{L} = 5 \text{ V}, V_{IN} = 2.4 \text{ V}, 0.8 \text{ V}^{f}$ | | | MIN. d | MAX. d | MIN. d | MAX.d | |
| Analog Switch | • | | | • | | | | | |
| Analog Signal Range ^e | V _{ANALOG} | | Full | - | 0 | 12 | 0 | 12 | ٧ |
| Drain-Source On-Resistance | R _{DS(on)} | V+ = 10.8 V, V- = 0 V $I_S = 10 \text{ mA}, V_D = 2/9 \text{ V}$ | Room Full | 16 | - | 26 40 | - | 26 35 | Ω |
| On resistance | | ig = 10 mz, v _D = 2/3 v | | | - | | - | | |
| | I _{S(off)} | | Room | - | -1 | 1 | -1 | 1 | |
| Switch Off Leakage Current | | $V_D = 1/11 \text{ V}, V_S = 11/1 \text{ V}$ | Full | - | -15 | 15 | -10 | 10 | |
| - | I _{D(off)} | | Room | - | -1 | 1 | -1 | 1 | nA |
| | B(OII) | | Full | - | -15 | 15 | -10 | 10 | |
| Channel On Leakage | I _{D(on)} | $V_S = V_D = 11/1 V$ | Room | - | -1 | 1 | -1 | 1 | |
| Current | 10(011) | | Full | - | -15 | 15 | -10 | 10 | |
| Digital Control | _ | | | 1 | T | T | ı | | |
| Input Current, VIN Low | I _{IL} | V _{IN} under test = 0.8 V | Full | 0.01 | -1.5 | 1.5 | -1 | 1 | μA |
| Input Current, VIN High | I _{IH} | V _{IN} under test = 2.4 V | Full | | -1.5 | 1.5 | -1 | 1 | μ/ι |
| Dynamic Characteristics | | | | | | | | | |
| Turn-On Time | + | | Room | 16 | - | 50 | - | 50 | - ns |
| rum-on nine | t _{ON} | R_L = 300 Ω, C_L = 35 pF, V_S = 5 V, see figure 2 | Full | - | - | 70 | - | 60 | |
| T O# Time - | | | Room | 9 | - | 30 | - | 30 | |
| Turn-Off Time | t _{OFF} | | Full | - | - | 48 | - | 40 | |
| Break-Before-Make Time Delay | t _D | DG413L only, $V_S = 5 V$, $R_L = 300 \Omega$, $CL = 35 pF$ | Room | 5 | - | - | - | - | |
| Charge Injection e | Q | $V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 10 \text{ nF}$ | Room | 6.6 | - | - | - | - | рС |
| Off-Isolation e | OIRR | | Room | 68.4 | - | - | - | - | |
| Channel-to-Channel Crosstalk ^e | X _{TALK} | $R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$ | Room | 114 | - | - | - | - | dB |
| Source Off Capacitance e | C _{S(off)} | | Room | 5 | - | - | - | - | |
| Drain Off Capacitance e | C _{D(off)} | f = 1 MHz | Room | 6 | - | - | - | - | рF |
| Channel-On Capacitance e | C _{D(on)} | | Room | 15 | - | - | - | - | |
| Power Supplies | 2(0.1) | | | | | | 1 | | |
| • • | | | Room | 0.02 | - | 1 | _ | 1 | |
| Positive Supply Current | l+ | | Full | - | - | 7.5 | - | 5 | |
| | | | Room | -0.002 | -1 | - | -1 | - | |
| Negative Supply Current | l- | | Full | - | -7.5 | - | -5 | - | |
| Logic Supply Current | l. | $V_{IN} = 0 \text{ V or 5 V}$ | Room | 0.002 | - | 1 | - | 1 | μA |
| Logic Supply Current | IL | | Full | - | - | 7.5 | - | 5 | |
| Ground Current | la | | Room | -0.002 | -1 | - | -1 | - | |
| Ground Current | I _{GND} | | Full | - | -7.5 | - | -5 | - | |

- a. Refer to PROCESS OPTION FLOWCHART
- b. Room = 25 °C, full = as determined by the operating temperature suffix
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet
- e. Guaranteed by design, not subject to production test
- f. V_{IN} = input voltage to perform proper function
- g. Leakage parameters are guaranteed by worst case test conditions and not subject to test



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| SPECIFICATIONS a (Dual Supply ± 5 V) | | | | | | | | | |
|--|---------------------|---|------|--------|--------|--------------------------|--------|---------------------------|------|
| PARAMETER | SYMBOL | | | TYP. ° | LIM | IFFIX IITS +125 °C | LIN | IFFIX IITS o +85 °C | UNIT |
| | | V+ = 5 V, V- = -5 V $V_L = 5 V, V_{IN} = 2.4 V, 0.8 V^f$ | | | MIN. d | MAX. d | MIN. d | MAX. d | |
| Analog Switch | | | | | I. | | | | |
| Analog Signal Range ^e | V _{ANALOG} | | Full | - | -5 | 5 | -5 | 5 | V |
| Drain-Source | R _{DS(on)} | V+ = 5 V, V- = -5 V, | Room | 18 | - | 30 | - | 30 | Ω |
| On-Resistance | 20(0.1) | $I_S = 10 \text{ mA}, V_D = \pm 3.5 \text{ V}$ | Full | - | - | 42 | - | 37 | |
| | I _{S(off)} | | Room | - | -1 | 1 | -1 | 1 | |
| Switch Off | 0(011) | V+ = 5.5, V- = -5.5 V, | Full | - | -15 | 15 | -10 | 10 | |
| Leakage Current ^g | I _{D(off)} | $V_D = \pm 4.5 \text{ V}, V_S = \pm 4.5 \text{ V}$ | Room | - | -1 | 1 | -1 | 1 | nA |
| | ·D(OII) | | Full | - | -15 | 15 | -10 | 10 | |
| Channel On | l | V+ = 5.5 V, V- = -5.5 V, | Room | - | -1 | 1 | -1 | 1 | |
| Leakage Current ^g | I _{D(on)} | $V_S = V_D = \pm 4.5 \text{ V}$ | Full | - | -15 | 15 | -10 | 10 | |
| Digital Control | | | | | | | | | |
| Input Current, V _{IN} Low ^e | I _{IL} | V _{IN} under test = 0.8 V | Full | 0.05 | -1.5 | 1.5 | -1 | 1 | |
| Input Current, V _{IN} High ^e | I _{IH} | V _{IN} under test = 2.4 V | Full | 0.05 | -1.5 | 1.5 | -1 | 1 | μA |
| Dynamic Characteristics | | | | | | | | | |
| T 0 T 0 | | $R_L = 300 \Omega$, $C_L = 35 pF$, $V_S = \pm 3.5 V$, see figure 2 | Room | 17 | - | 50 | - | 50 | |
| Turn-On Time ^e | t _{ON} | | Full | - | - | 70 | - | 60 | |
| | | | Room | 12 | - | 35 | - | 35 | |
| Turn-Off Time ^e | t _{OFF} | | Full | - | - | 50 | - | 40 | ns |
| Break-Before-Make Time Delay ^e | t _D | DG413L only, $V_S = 3.5 \text{ V}$, $R_L = 300 \Omega$, $C_L = 35 \text{ pF}$ | Room | 5 | - | - | - | - | |
| Charge Injection ^e | Q | $V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 10 \text{ nF}$ | Room | 5.8 | - | - | - | - | рС |
| Off Isolation e | OIRR | 3 | Room | 68 | - | - | - | - | |
| Channel-to-Channel Crosstalk ^e | X _{TALK} | $R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$ | Room | 113 | - | - | - | - | dB |
| Source Off Capacitance e | C _{S(off)} | | Room | 5 | - | - | - | - | |
| Drain Off Capacitance e | C _{D(off)} | f = 1 MHz | Room | 6 | - | - | - | - | рF |
| Channel On Capacitance e | C _{D(on)} | | Room | 14 | - | - | - | - | |
| Power Supplies | . , , | | | | | | | | |
| o . o | | | Room | 0.03 | - | 1 | - | 1 | |
| Positive Supply Current e | I+ | | Full | - | - | 7.5 | - | 5 | |
| | | | Room | -0.002 | -1 | - | -1 | - | |
| Negative Supply Current ^e | I- | ., | Full | - | -7.5 | - | -5 | - | |
| Lania Ormania Ormania | , | $V_{IN} = 0 \text{ V or 5 V}$ | Room | 0.002 | - | 1 | - | 1 | μA |
| Logic Supply Current e | IL | | Full | - | - | 7.5 | - | 5 | |
| | | | Room | -0.002 | -1 | - | -1 | - | |
| Ground Current e | I _{GND} | | Full | - | -7.5 | - | -5 | - | |

- a. Refer to PROCESS OPTION FLOWCHART
- b. Room = 25 °C, full = as determined by the operating temperature suffix
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet
- e. Guaranteed by design, not subject to production test
- f. V_{IN} = input voltage to perform proper function
- g. Leakage parameters are guaranteed by worst case test conditions and not subject to test



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| SPECIFICATIONS ^a (Single Supply 5 V) | | | | | | | | | | | | | |
|---|-------------------------|--|----------|--------|--------|--------|--------|--------|-----|-------------------------|-----|---------------------------|------|
| PARAMETER | SYMBOL | TEST CONDITIONS UNLESS OTHERWISE SPECIFIED | TEMP.b 1 | TEMP.b | TEMP.b | TEMP.b | TEMP.b | TYP. ° | LIN | IFFIX IITS +125°C | LIM | IFFIX IITS o +85 °C | UNIT |
| | | V+ = 5 V, V- = 0 V $V_L = 5 V, V_{IN} = 2.4 V, 0.8 V^f$ | | | MIN. d | MAX. d | MIN. d | MAX. d | | | | | |
| Analog Switch | | | | | | | | | | | | | |
| Analog Signal Range ^e | V _{ANALOG} | | Full | - | - | 5 | ı | 5 | > | | | | |
| Drain-Source | B-a/ | V+ = 4.5 V, | Room | 36 | - | 50 | ı | 50 | Ω | | | | |
| On-Resistance e | R _{DS(on)} | $I_S = 5 \text{ mA}, V_D = 1 \text{ V}, 3.5 \text{ V}$ | Full | - | - | 88 | - | 75 | 22 | | | | |
| Dynamic Characteristics | Dynamic Characteristics | | | | | | | | | | | | |
| Turn-On Time ^e | t _{ON} | | Room | 27 | - | 50 | - | 50 | | | | | |
| Turn on time | ON | $R_L = 300 \Omega$, $C_L = 35 pF$, | Hot | - | - | 90 | - | 60 | | | | | |
| Turn-Off Time ^e | t _{OFF} | $V_S = 3.5 \text{ V}$, see figure 2 | Room | 15 | - | 30 | - | 30 | ns | | | | |
| Tuni on Timo | OFF | OFF | Hot | - | - | 55 | - | 40 | | | | | |
| Break-Before-Make Time Delay ^e | t _D | DG413L only, V_S = 3.5 V, R_L = 300 Ω , C_L = 35 pF | Room | 11 | - | - | - | - | | | | | |
| Charge Injection ^e | Q | $V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 10 \text{ nF}$ | Room | 3.3 | - | - | - | - | рC | | | | |
| Power Supplies | | | | | | | | | | | | | |
| Positive Supply Current e | l+ | | Room | 0.02 | - | 1 | ı | 1 | | | | | |
| Tositive Supply Current | IΤ | | Hot | - | - | 7.5 | - | 5 | | | | | |
| Negative Supply Current e | I- | | Room | -0.002 | -1 | - | -1 | - | | | | | |
| Negative Supply Current | I- | $V_{IN} = 0 \text{ V or 5 V}$ | Hot | - | -7.5 | - | -5 | - | μΑ | | | | |
| Logic Supply Current ^e | | VIN — U V OI U V | Room | 0.002 | - | 1 | ı | 1 | μΛ | | | | |
| Logic Supply Current | lι | | Hot | - | - | 7.5 | ı | 5 | | | | | |
| Ground Current e | I _{GND} | | Room | -0.002 | -1 | - | -1 | - | | | | | |
| Ground Gurrent | GND | | Hot | - | -7.5 | - | -5 | - | | | | | |

- a. Refer to PROCESS OPTION FLOWCHART
- b. Room = 25 $^{\circ}$ C, full = as determined by the operating temperature suffix
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing
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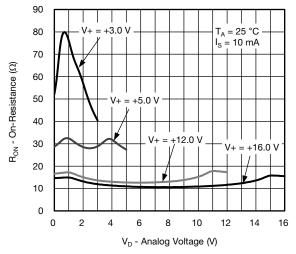


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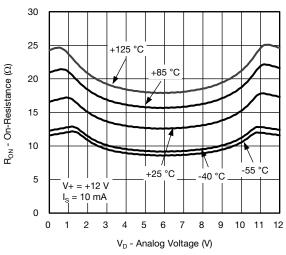
| SPECIFICATIONS a (Single Supply 3 V) | | | | | | | | | |
|--|---------------------|---|--------------|-------|----------------------------------|------------|--------|---------------------------|------|
| PARAMETER | SYMBOL | TEST CONDITIONS UNLESS OTHERWISE SPECIFIED | TEMP. b TYP. | | ASUFFIX LIMITS -55 °C to +125 °C | | LIM | IFFIX IITS D +85 °C | UNIT |
| | | V+ = 3 V, V- = 0 V $V_L = 3 V, V_{IN} = 0.4 V, 2.0 V^f$ | | | MIN. d | MAX. d | MIN. d | MAX. d | |
| Analog Switch | • | | | | | | | | |
| Analog Signal Range ^e | V _{ANALOG} | | Full | 1 | 0 | 3 | 0 | 3 | V |
| Drain-Source On-Resistance | R _{DS(on)} | V+ = 2.7 V, V- = 0 V, $I_S = 5 \text{ mA}, V_D = 0.5, 2.2 \text{ V}$ | Room Full | 106 | - | 130 150 | - | 130 140 | Ω |
| | | | Room | - | -1 | 1 | -1 | 1 | |
| Switch Off | I _{S(off)} | V+ = 3.3, V- = 0 V, | Full | - | -15 | 15 | -10 | 10 | |
| Leakage Current ^g | | $V_D = 1, 2 \text{ V}, V_S = 2, 1 \text{ V}$ | Room | - | -1 | 1 | -1 | 1 | A |
| | I _{D(off)} | | Full | - | -15 | 15 | -10 | 10 | nA |
| Channel On | | V+ = 3.3 V, V- = 0 V, | Room | - | -1 | 1 | -1 | 1 | |
| Leakage Current ^g | I _{D(on)} | $V_S = V_D = 1, 2 V$ | Full | - | -15 | 15 | -10 | 10 | |
| Digital Control | | | | | | | | | |
| Input Current, V _{IN} Low | I _{IL} | V _{IN} under test = 0.4 V | Full | 0.005 | -1.5 | 1.5 | -1 | 1 | μA |
| Input Current, V _{IN} High | I _{IH} | V _{IN} under test = 2.4 V | Full | 0.005 | -1.5 | 1.5 | -1 | 1 | μΛ |
| Dynamic Characteristics | | | | | | | | | |
| Turn-On Time | t _{ON} | | Room | 57 | - | 85 | - | 85 | |
| Turri on Time | UN | $R_L = 300 \Omega, C_L = 35 pF,$ | Full | - | - | 150 | - | 110 | |
| Turn-Off Time | t _{OFF} | $V_S = 1.5 V$, see figure 2 | Room | 25 | - | 60 | - | 60 | ns |
| Tuni on Time | OFF | | Full | - | - | 100 | - | 85 | |
| Break-Before-Make Time Delay | t _D | DG413L only, $V_S = 1.5 \text{ V}$, $R_L = 300 \Omega$, $C_L = 35 \text{ pF}$ | Room | 24 | - | - | - | - | |
| Charge Injection ^e | Q | $V_g = 0 \text{ V}, R_g = 0 \Omega, C_L = 10 \text{ nF}$ | Room | 2 | - | - | - | ı | рC |
| Off Isolation e | OIRR | | Room | 68 | - | - | - | 1 | |
| Channel-to-Channel Crosstalk ^e | X _{TALK} | $R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$ | Room | 107 | - | - | - | - | dB |
| Source Off Capacitance e | C _{S(off)} | | Room | 6 | - | - | - | - | |
| Drain Off Capacitance e | C _{D(off)} | f = 1 MHz | Room | 7 | - | - | - | - | pF |
| Channel On Capacitance e | C _{D(on)} | | Room | 15 | - | - | - | - | |

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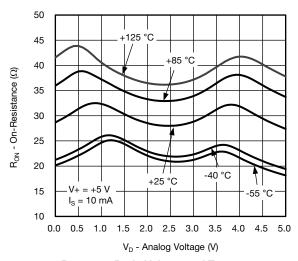
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



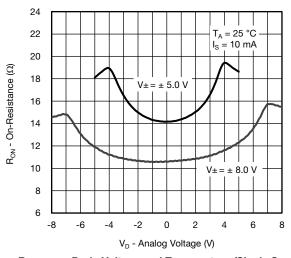
R_{DS(on)} vs. Drain Voltage (Single Supply)



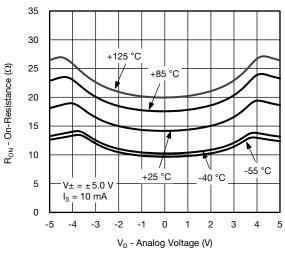
R_{DS(on)} vs. Drain Voltage and Temperature



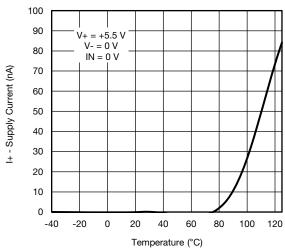
 $R_{DS(on)}$ vs. Drain Voltage and Temperature



R_{DS(on)} vs. Drain Voltage and Temperature (Single Supply)

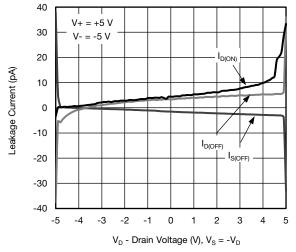


Supply Current vs. Temperature

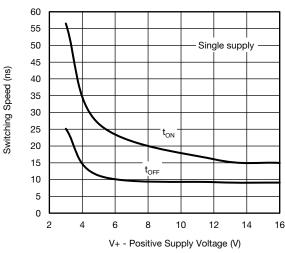


Switching Time vs. Single Supply

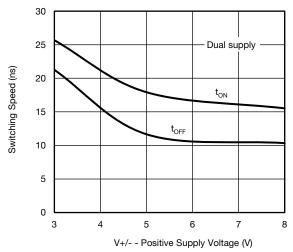
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



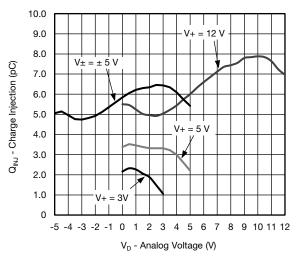
Leakage Current vs. Drain Voltage



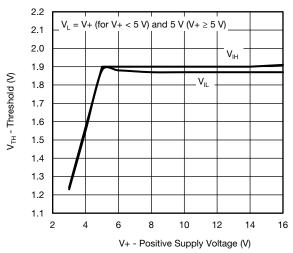
Switching Time vs. Single Supply Voltage



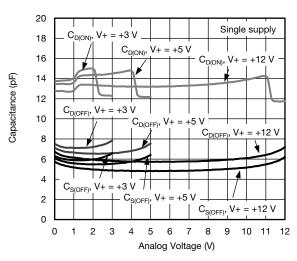
Switching Time vs. Dual Supply Voltage



Charge Injection vs. Drain Voltage



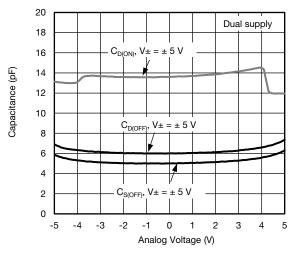
Threshold vs. Single Supply Current

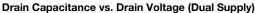


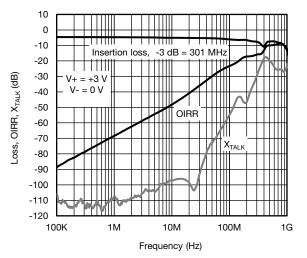
Drain Capacitance vs. Drain Voltage (Single Supply)

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

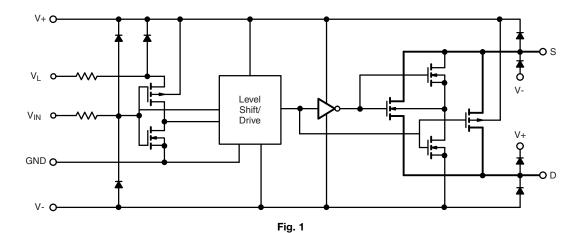




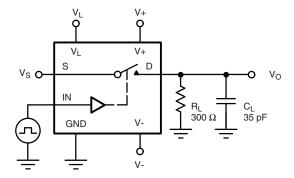


Insertion Loss, Off Isolation and Crosstalk vs. Frequency

SCHEMATIC DIAGRAM (Typical Channel)

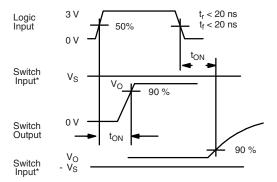


TEST CIRCUITS



C_L (includes fixture and stray capacitance)

$$V_0 = V_S$$
 $R_L + r_{DS(on)}$



Note: Logic input waveform is inverted for switches that have the opposite logic sense control

Fig. 2 - Switching Time

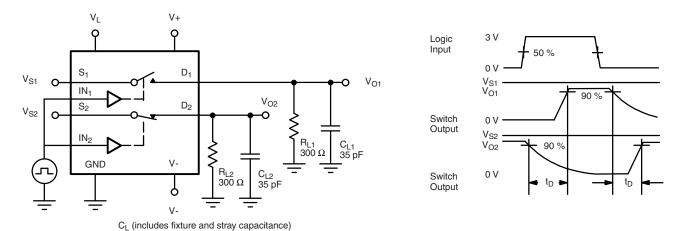
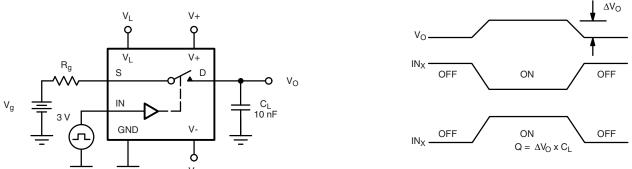


Fig. 3 - Break-Before-Make (DG413LE)



 $\ensuremath{\mathsf{IN}_X}$ dependent on switch configuration Input polarity determined by sense of switch.

Fig. 4 - Charge Injection

TEST CIRCUITS

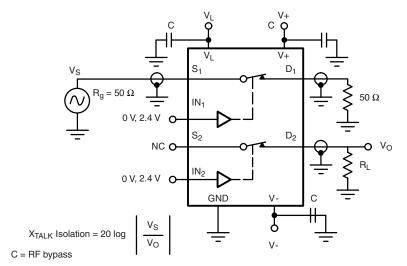


Fig. 5 - Crosstalk

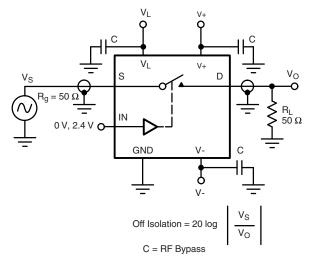


Fig. 6 - Off-Isolation

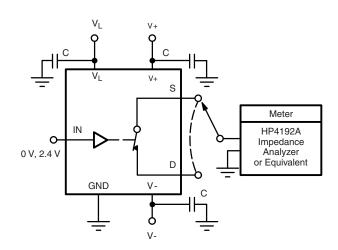
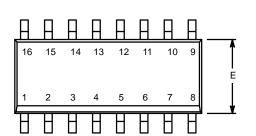


Fig. 7 - Source / Drain Capacitances

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg278091.



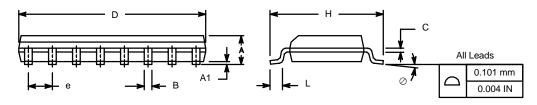
SOIC (NARROW): 16-LEAD
JEDEC Part Number: MS-012



| | MILLIM | MILLIMETERS | | HES | | | |
|--------------------------------|--------|--------------------|-------|-------|--|--|--|
| Dim | Min | Max | Min | Max | | | |
| Α | 1.35 | 1.75 | 0.053 | 0.069 | | | |
| A ₁ | 0.10 | 0.20 | 0.004 | 0.008 | | | |
| В | 0.38 | 0.51 | 0.015 | 0.020 | | | |
| С | 0.18 | 0.23 | 0.007 | 0.009 | | | |
| D | 9.80 | 10.00 | 0.385 | 0.393 | | | |
| E | 3.80 | 4.00 | 0.149 | 0.157 | | | |
| е | 1.27 | BSC | 0.050 | BSC | | | |
| Н | 5.80 | 6.20 | 0.228 | 0.244 | | | |
| L | 0.50 | 0.93 | 0.020 | 0.037 | | | |
| 0 | 0° | 8° | 0° | 8° | | | |
| FCN: S-03946—Rev. F. 09-Jul-01 | | | | | | | |

ECN: S-03946—Rev. F, 09-Jul-01

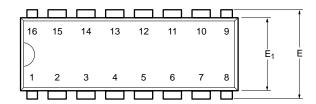
DWG: 5300

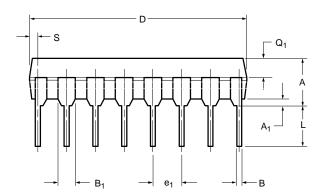


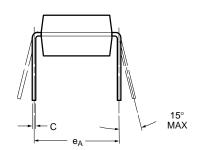
Document Number: 71194 www.vishay.com 02-Jul-01 sww.vishay.com



PDIP: 16-LEAD





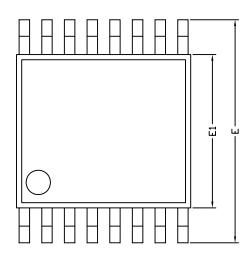


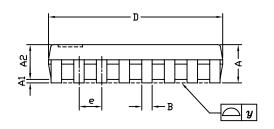
| | MILLIM | IETERS | INCHES | | | |
|---|--------|--------|--------|-------|--|--|
| Dim | Min | Max | Min | Max | | |
| Α | 3.81 | 5.08 | 0.150 | 0.200 | | |
| A ₁ | 0.38 | 1.27 | 0.015 | 0.050 | | |
| В | 0.38 | 0.51 | 0.015 | 0.020 | | |
| B ₁ | 0.89 | 1.65 | 0.035 | 0.065 | | |
| С | 0.20 | 0.30 | 0.008 | 0.012 | | |
| D | 18.93 | 21.33 | 0.745 | 0.840 | | |
| Е | 7.62 | 8.26 | 0.300 | 0.325 | | |
| E ₁ | 5.59 | 7.11 | 0.220 | 0.280 | | |
| e ₁ | 2.29 | 2.79 | 0.090 | 0.110 | | |
| e _A | 7.37 | 7.87 | 0.290 | 0.310 | | |
| L | 2.79 | 3.81 | 0.110 | 0.150 | | |
| Q_1 | 1.27 | 2.03 | 0.050 | 0.080 | | |
| S | 0.38 | 1.52 | .015 | 0.060 | | |
| ECN: S-03946—Rev. D, 09-Jul-01 DWG: 5482 | | | | | | |

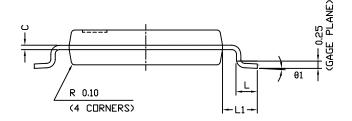
Document Number: 71261 www.vishay.com 06-Jul-01 sum.vishay.com



TSSOP: 16-LEAD







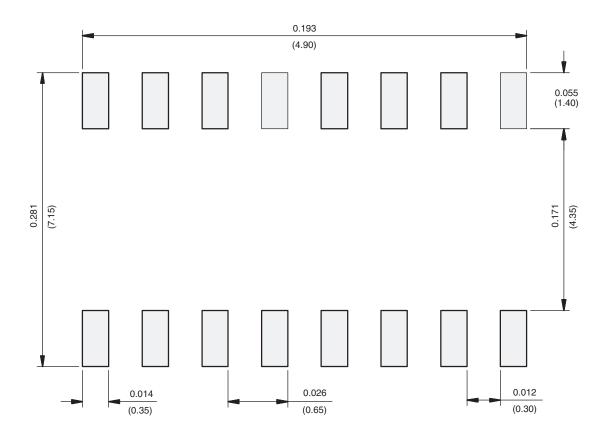
| | DIMENSIONS IN MILLIMETERS | | | | | | |
|---------------------------|---------------------------|-------|------|--|--|--|--|
| Symbols | Min | Nom | Max | | | | |
| Α | - | 1.10 | 1.20 | | | | |
| A1 | 0.05 | 0.10 | 0.15 | | | | |
| A2 | = | 1.00 | 1.05 | | | | |
| В | 0.22 | 0.28 | 0.38 | | | | |
| С | = | 0.127 | - | | | | |
| D | 4.90 | 5.00 | 5.10 | | | | |
| E | 6.10 | 6.40 | 6.70 | | | | |
| E1 | 4.30 | 4.40 | 4.50 | | | | |
| е | - | 0.65 | - | | | | |
| L | 0.50 | 0.60 | 0.70 | | | | |
| L1 | 0.90 | 1.00 | 1.10 | | | | |
| у | = | - | 0.10 | | | | |
| θ1 | 0° | 3° | 6° | | | | |
| ECN: S-61920-Rev. D. 23-0 | Oct-06 | | | | | | |

DWG: 5624

Document Number: 74417 www.vishay.com 23-Oct-06



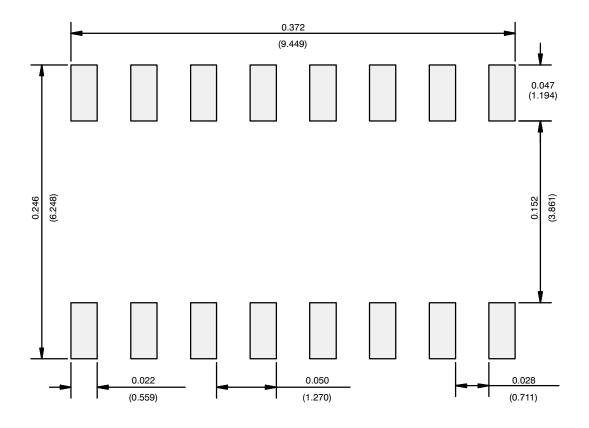
RECOMMENDED MINIMUM PAD FOR TSSOP-16



Recommended Minimum Pads Dimensions in inches (mm)



RECOMMENDED MINIMUM PADS FOR SO-16



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

APPLICATION NOTE

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Vishay

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